

Abstract**Method for Pulling a Silicon Single Crystal**

5 The invention relates to a method for pulling a silicon single
crystal from a melt which is contained in a crucible,
comprising
immersion of a seed crystal into the melt;
crystallization of the single crystal on the seed crystal by
10 raising the seed crystal from the melt with a crystal pull
speed;
widening the diameter of the single crystal to a setpoint
diameter in a conical section, comprising
control of the crystal pull speed in such a way as to induce a
15 curvature inversion of a growth front of the single crystal in
the conical section.

Fig. 1